

RESIST COMPOSITION AND PATTERNING PROCESS

ABSTRACT OF THE DISCLOSURE

The present invention relates to: a resist composition such as a chemically amplified resist composition for providing an excellent pattern profile even at a substrate-side boundary face of resist, in addition to a higher resolution in photolithography for micro-fabrication, and particularly in photolithography adopting, as an exposure source, KrF laser, ArF laser, F₂ laser, ultra-short ultraviolet light, electron beam, X-rays, or the like; and a patterning process utilizing the resist composition. The present invention provides a chemically amplified resist composition comprising one or more kinds of amine compounds or amine oxide compounds (except for those having a nitrogen atom of amine or amine oxide included in a ring structure of an aromatic ring) at least having a carboxyl group and having no hydrogen atoms covalently bonded to a nitrogen atom as a basic center.

Figure : None